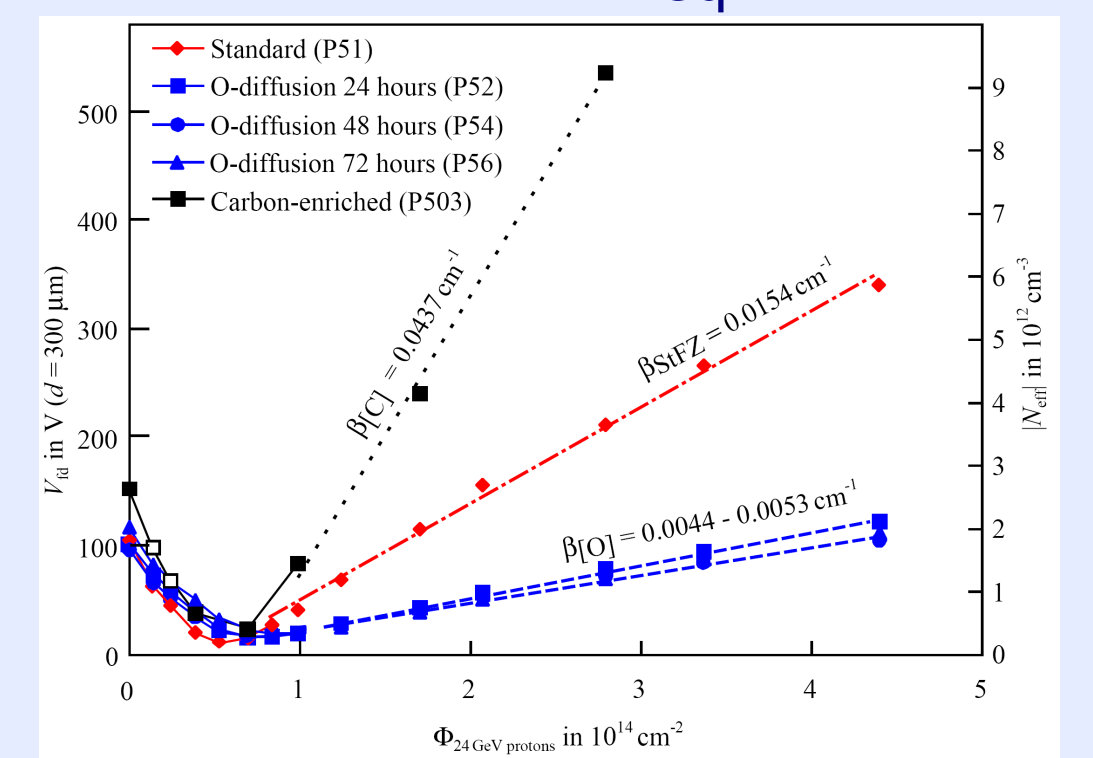


Test Beam Results with 3D Silicon Strip Detectors

Michael Köhler (University of Freiburg, Germany)

Motivation: More Radiation Hardness Needed...

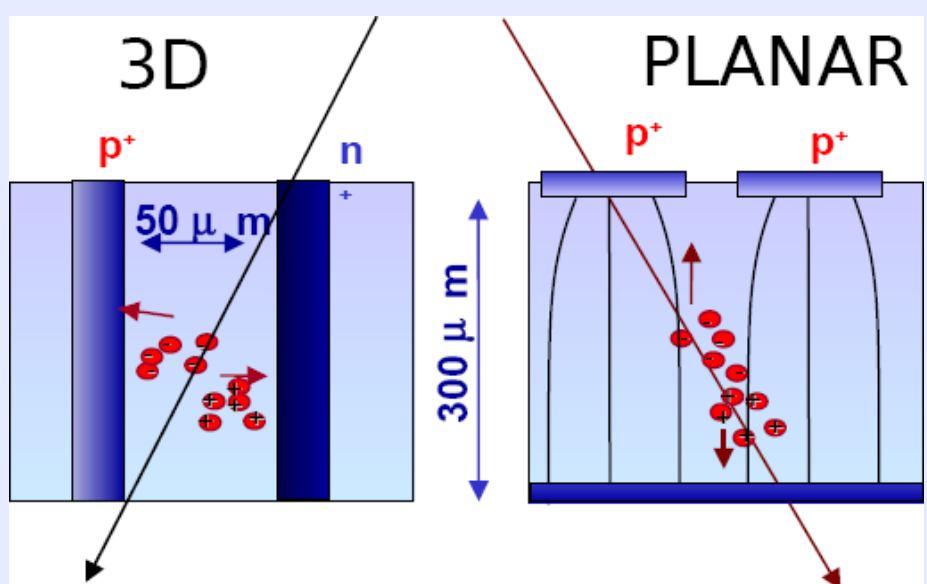
- Upgrade of the LHC (~2018): **super LHC** (sLHC), peak luminosity increased tenfold ($L=10^{35} \text{ s}^{-1} \text{ cm}^{-2}$)
→ Extremely high track density, **severe radiation damage** especially for the silicon tracking detectors
- ATLAS: current SCT (SemiConductor Tracker, silicon strip detector) designed for fluence of $10^{14} \text{ n}_{\text{eq}}/\text{cm}^2$
→ For the sLHC: **inner strip sensors must withstand $10^{15} \text{ n}_{\text{eq}}/\text{cm}^2$** (factor of 10!)
- Main effects of radiation damage in silicon:
 - Voltage to achieve **full depletion** of the sensor increases
 - **Trapping** increases: free charge carriers get trapped at crystal defects
- Possible solutions: radiation harder material (e.g. oxygen enriched, p-type silicon), modified geometry (3D, see below)



[A. Ruzin, NIMA 447 (2000)]

3D Detectors

- Idea: decoupling of detector thickness and charge collection distance
- Columnar electrodes etched into the wafer

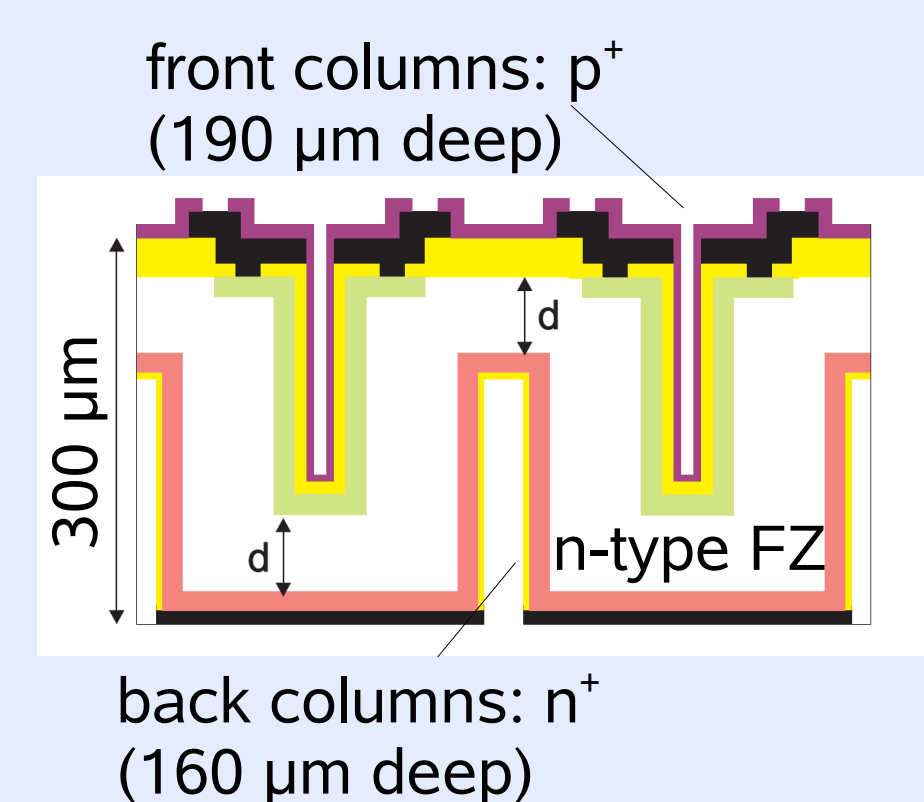


Advantages:

- **Lower depletion voltage**
- **Less affected by trapping**
- Effects of radiation damage reduced
- But: fabrication challenging!

- Process simplification: **3D DDTC detectors**

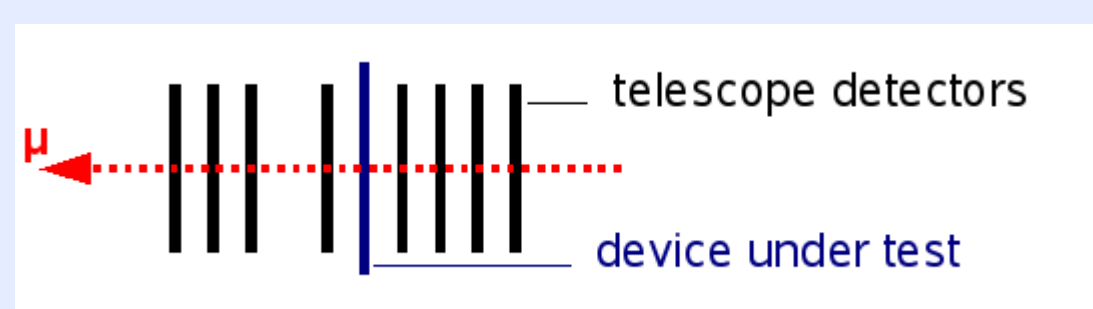
- DDTC: double sided, double type columns - columns not etched through the sensor completely
- Device under test: **microstrip detector**, 100 um pitch; fabricated by FBK-IRST, Trento (Italy)



[A. Zoboli, NIMA, in press]

Test Beam

- July 2008: **test beam at the CERN SPS**, H2 beamline (225 GeV/c muons)
- **Silicon Beam Telescope** (SiBT, provided by the university of Helsinki): delivering track position with a resolution of $\sim 4 \mu\text{m}$

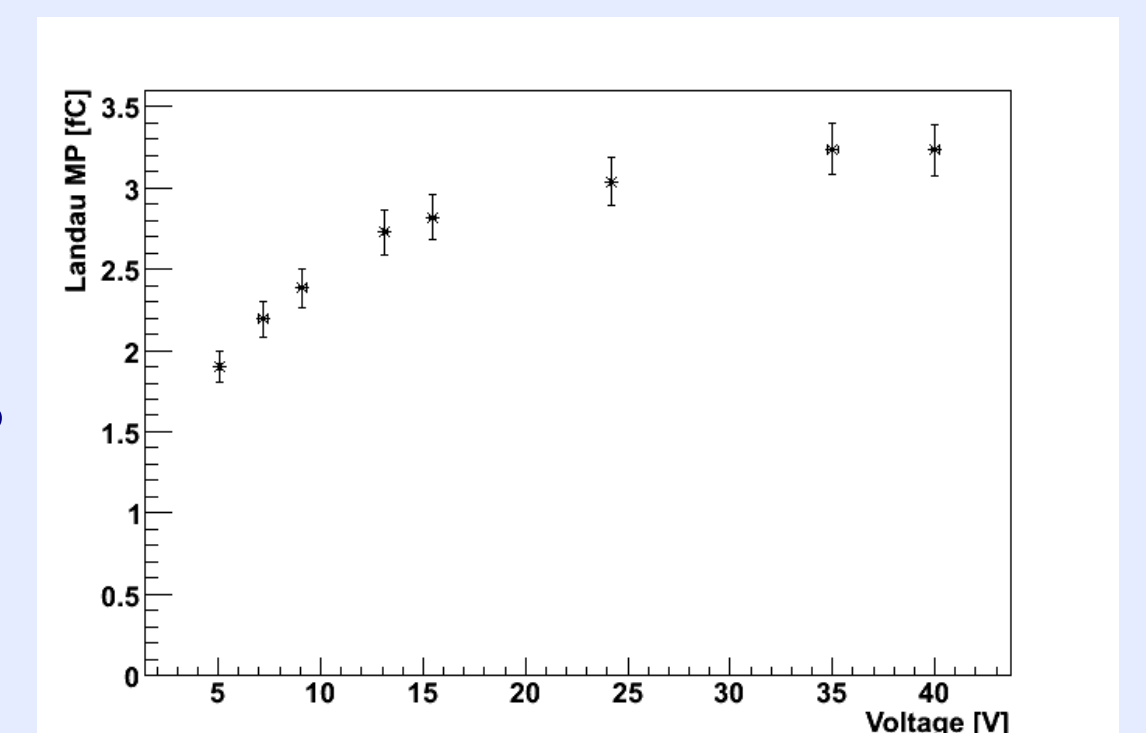


- Readout: APV25 chip (CMS tracker)
- Purpose: **position resolved studies of the detector behaviour** (charge collection, efficiency ...) in a realistic environment

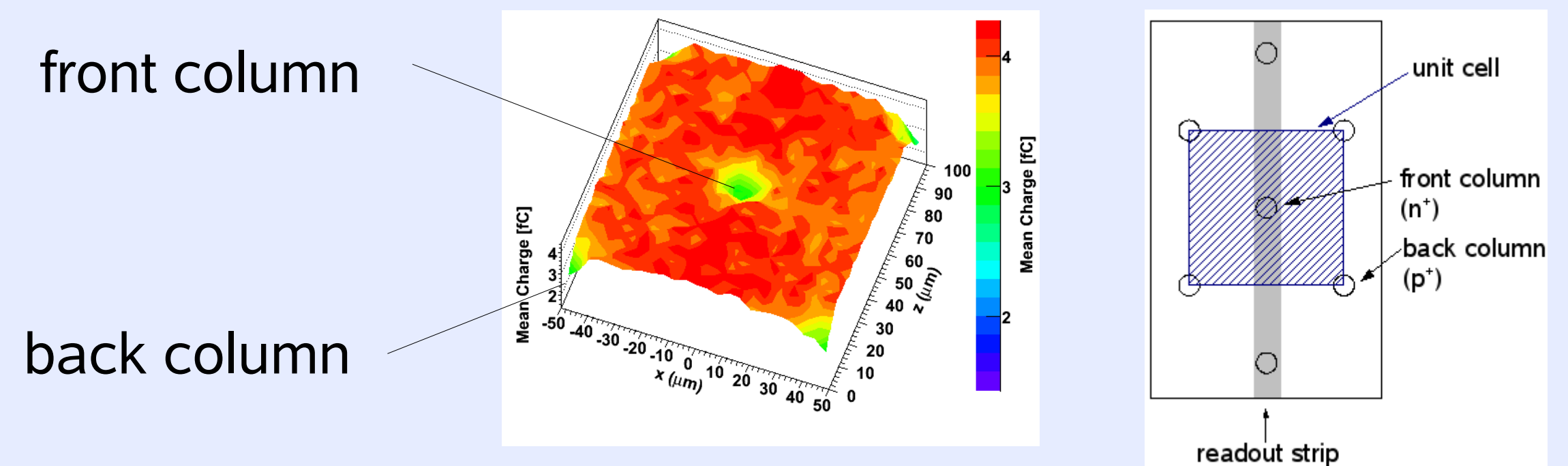
Test Beam Results

- Key questions:
 - Does the **collected charge** correspond to the value expected for 300 um silicon ($\sim 3.5 \text{ fC}$)?
 - Is the charge collection and the **efficiency uniform**?

- **Signal** (Landau MP) for bias voltages from 5 V to 40 V
 - Max. collected charge: $\sim 3.2 \text{ fC}$
 - Close to expectation, 10% loss due to asynchronous beam
 - S/N: ~ 15

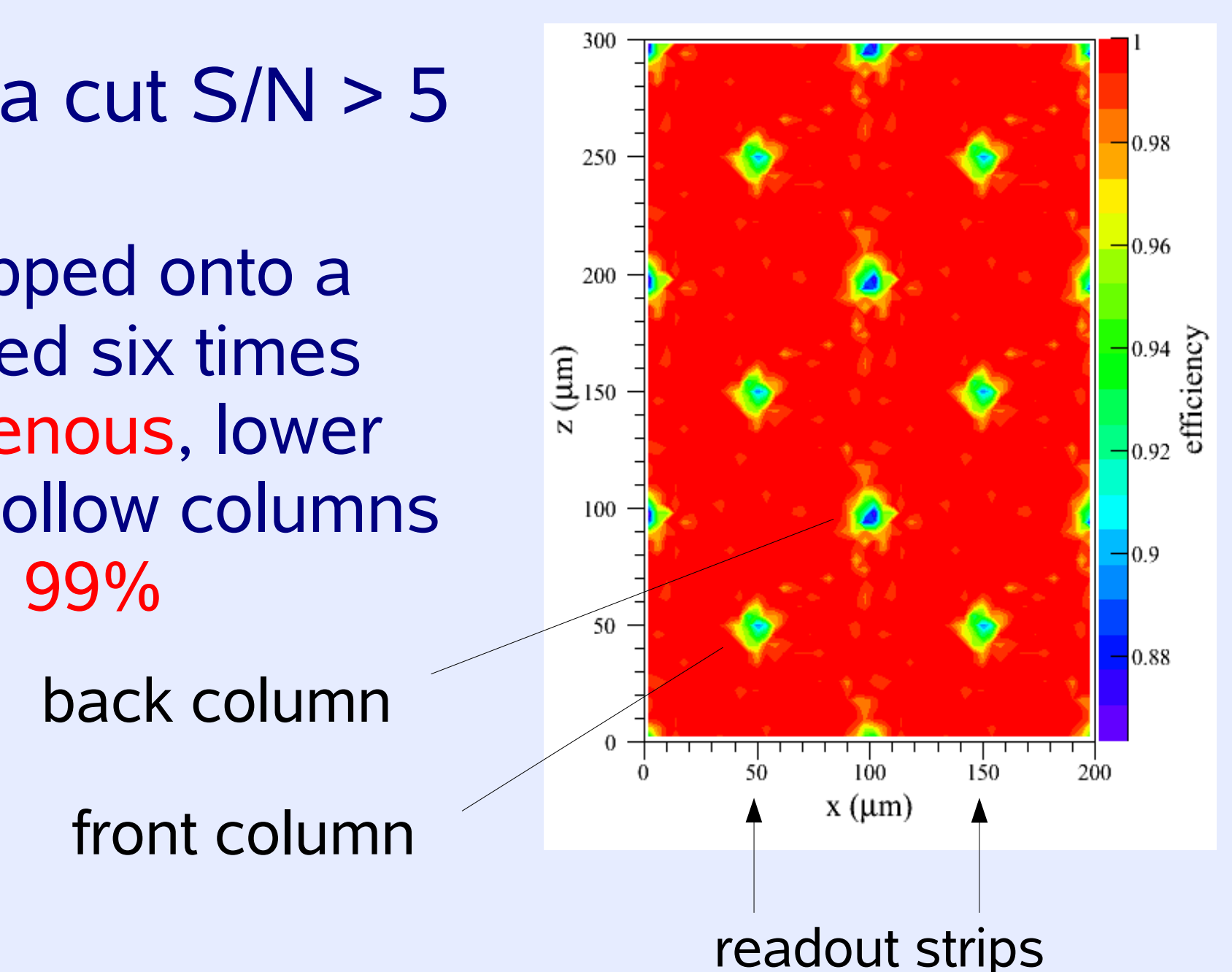


- Mean value (not Landau MP!) of **collected charge** mapped onto a 2D unit cell, 3-strip-clusters: **uniformly distributed**, hollow columns visible



- **2D efficiency** for a cut $S/N > 5$ ($Q > 1 \text{ fC}$)

- Entire sensor mapped onto a unit cell, then plotted six times
- **Efficiency homogenous**, lower efficiency only in hollow columns
- Overall efficiency: **99%**



Conclusion and Outlook

- Test beam results show: **3D DDTC detectors meet the expectations** concerning spatially resolved charge collection and efficiency
- Plan for summer 2009: perform another **test beam with planar and 3D DDTC strip detectors** (irradiated and unirradiated)
→ Direct comparison of the radiation hardness of both detector types